

Tanemasa Asano

List of Publications by Year in descending order

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257450

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230
docs citations

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times ranked

1176
citing authors

#	ARTICLE	IF	CITATIONS
1	Silicon/insulator heteroepitaxial structures formed by vacuum deposition of CaF ₂ and Si. Applied Physics Letters, 1982, 40, 66-68.	3.3	154
2	Heteroepitaxial Growth of Group-IIa-Fluoride Films on Si Substrates. Japanese Journal of Applied Physics, 1983, 22, 1474-1481.	1.5	108
3	Epitaxial relations in group-IIIa fluoride/Si(111) heterostructures. Applied Physics Letters, 1983, 42, 517-519.	3.3	89
4	Epitaxial growth of Si films on CaF ₂ /Si structures with thin Si layers predeposited at room temperature. Journal of Applied Physics, 1984, 55, 3566-3570.	2.5	80
5	In situ observation of nickel metal-induced lateral crystallization of amorphous silicon thin films. Applied Physics Letters, 2002, 80, 944-946.	3.3	77
6	Single Crystalline Silicide Formation. Japanese Journal of Applied Physics, 1981, 20, 1649-1656.	1.5	66
7	Ni-imprint induced solid-phase crystallization in Si _{1-x} Gex (x: 0≤x<1) on insulator. Applied Physics Letters, 2007, 91, .	3.3	60
8	Electron-Beam Exposure (EBE) and Epitaxy of GaAs Films on CaF ₂ /Si Structures. Japanese Journal of Applied Physics, 1988, 27, 1616-1625.	1.5	53
9	Enhanced nucleation in solid-phase crystallization of amorphous Si by imprint technology. Applied Physics Letters, 2000, 76, 3774-3776.	3.3	49
10	Field emission from ion-milled diamond films on Si. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 431.	1.6	46
11	Supramolecular Hybrid of Gold Nanoparticles and Semiconducting Single-Walled Carbon Nanotubes Wrapped by a Porphyrin-Fluorene Copolymer. Journal of the American Chemical Society, 2011, 133, 14771-14777.	13.7	46
12	Formation of GaAs-on-Insulator Structures on Si Substrates by Heteroepitaxial Growth of CaF ₂ and GaAs. Japanese Journal of Applied Physics, 1986, 25, L139-L141.	1.5	44
13	Investigation on Bistability and Fabrication of Bistable Prestressed Curved Beam. Japanese Journal of Applied Physics, 2008, 47, 5291.	1.5	41
14	Schottky Source/Drain SOI MOSFET with Shallow Doped Extension. Japanese Journal of Applied Physics, 2003, 42, 2009-2013.	1.5	40
15	Lithium niobate ridged waveguides with smooth vertical sidewalls fabricated by an ultra-precision cutting method. Optics Express, 2014, 22, 27733.	3.4	40
16	Development and characterization of a flat laminate vapor chamber. Applied Thermal Engineering, 2016, 104, 461-471.	6.0	40
17	Flattening the Surface of CaF ₂ /Si(100) Structures by Post-Growth Annealing. Japanese Journal of Applied Physics, 1988, 27, 1193-1198.	1.5	36
18	Reduction of the Floating Body Effect in SOI MOSFETs by Using Schottky Source/Drain Contacts. Japanese Journal of Applied Physics, 1998, 37, 1295-1299.	1.5	35

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19	Fabrication of Back-Side Illuminated Complementary Metal Oxide Semiconductor Image Sensor Using Compliant Bump. Japanese Journal of Applied Physics, 2010, 49, 04DB01.	1.5	34
20	Epitaxial Growth of Ge Films onto CaF ₂ /Si Structures. Japanese Journal of Applied Physics, 1982, 21, L630-L632.	1.5	30
21	Epitaxial relations in Ca _x Sr _{1-x} F ₂ films grown on GaAs {111} and Ge(111) substrates. Applied Physics Letters, 1985, 46, 1131-1133.	3.3	30
22	Memory Device Using a Conducting Polymer and Solid Polymer Electrolyte. Japanese Journal of Applied Physics, 1991, 30, L215-L217.	1.5	28
23	Room-Temperature Cu Microjoining with Ultrasonic Bonding of Cone-Shaped Bump. Japanese Journal of Applied Physics, 2013, 52, 04CB10.	1.5	28
24	Thin-film lithium niobate-on-insulator waveguides fabricated on silicon wafer by room-temperature bonding method with silicon nanoadhesive layer. Optics Express, 2018, 26, 24413.	3.4	27
25	Formation of Thick, Thermally-Stable High-Resistivity-Layers in GaAs by Oxygen Ion Implantation. Japanese Journal of Applied Physics, 1981, 20, 901-907.	1.5	24
26	Growth behavior of boron-doped diamond in microwave plasma-assisted chemical vapor deposition using trimethylboron as the dopant source. Diamond and Related Materials, 1998, 7, 88-95.	3.9	24
27	Effects of Light Exposure during Anodization on Photoluminescence of Porous Si. Japanese Journal of Applied Physics, 1992, 31, L373-L375.	1.5	23
28	Synthesis and Electrical Properties of Phosphorus-Doped Homoepitaxial Diamond (111) by Microwave Plasma-Assisted Chemical Vapor Deposition Using Triethylphosphine as a Dopant Source. Japanese Journal of Applied Physics, 1998, 37, L543-L546.	1.5	23
29	Dehydration after Plasma Oxidation of Porous Low-Dielectric-Constant Spin-on-Glass Films. Japanese Journal of Applied Physics, 2000, 39, 3919-3923.	1.5	23
30	Room-temperature wafer bonding of LiNbO ₃ and SiO ₂ using a modified surface activated bonding method. Japanese Journal of Applied Physics, 2018, 57, 06HJ12.	1.5	23
31	Fabrication of Single-Crystal Si Microstructures by Anodization. Japanese Journal of Applied Physics, 1996, 35, 6648-6651.	1.5	20
32	Field Emission from an Ion-Beam-Modified Polyimide Film. Japanese Journal of Applied Physics, 1999, 38, L261-L263.	1.5	20
33	Fabrication of Micro Field Emitter Tip Using Ion-Beam Irradiation-Induced Self-Standing of Thin Films. Japanese Journal of Applied Physics, 2005, 44, 5744-5748.	1.5	20
34	Room-Temperature Cu-Cu Bonding in Ambient Air Achieved by Using Cone Bump. Applied Physics Express, 2011, 4, 016501.	2.4	20
35	Phosphorus doping of 4H SiC by liquid immersion excimer laser irradiation. Applied Physics Letters, 2013, 102, .	3.3	20
36	Room-temperature hermetic sealing by ultrasonic bonding with Au compliant rim. Japanese Journal of Applied Physics, 2014, 53, 06JM05.	1.5	20

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37	Patterning of CVD diamond films by seeding and their field emission properties. <i>Diamond and Related Materials</i> , 1994, 3, 1296-1300.	3.9	19
38	Behavior of Plated Microbumps during Ultrasonic Flip-Chip Bonding Determined from Dynamic Strain Measurement. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 2193-2197.	1.5	19
39	Ion Beam Modification of a Photoresist and Its Application to Field Emitters. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 7749-7753.	1.5	18
40	Fabrication of Carbon-Based Field Emitters Using Stamp Technology. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 7203-7207.	1.5	18
41	Inkjet Printing of Nickel Nanosized Particles for Metal-Induced Crystallization of Amorphous Silicon. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 6437-6443.	1.5	18
42	Formation of an Epitaxial Si/Insulator/Si Structure by Vacuum Deposition of CaF ₂ and Si. <i>Japanese Journal of Applied Physics</i> , 1982, 21, 187.	1.5	17
43	Field Emission from an Ion Irradiated Photoresist. <i>Japanese Journal of Applied Physics</i> , 1997, 36, L818-L820.	1.5	17
44	Structural Properties of Nickel Metal-Induced Laterally Crystallized Silicon Films and Their Improvement Using Excimer Laser Annealing. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 2592-2599.	1.5	17
45	Electrostatic Inkjet Patterning Using Si Needle Prepared by Anodization. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 5786-5790.	1.5	17
46	Location and Orientation Control of Si Grain by Combining Metal-Induced Lateral Crystallization and Excimer Laser Annealing. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 4347-4350.	1.5	17
47	Dynamic Strain and Chip Damage during Ultrasonic Flip Chip Bonding. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 3044-3048.	1.5	16
48	Characteristics of a Novel Compliant Bump for 3-D Stacking With High-Density Inter-Chip Connections. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2011, 1, 83-91.	2.5	16
49	Effect of laser annealing on photoluminescence properties of Phosphorus implanted ZnO nanorods. <i>Optics Express</i> , 2012, 20, 15247.	3.4	16
50	Phosphorus Doping into 4H-SiC by Irradiation of Excimer Laser in Phosphoric Solution. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 06GF02.	1.5	16
51	Investigation of the interface between LiNbO ₃ and Si wafers bonded by laser irradiation. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 088002.	1.5	16
52	Electrostatic Droplet Ejection Using Planar Needle Inkjet Head. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 5781-5785.	1.5	15
53	Residual Stress in Lithium Niobate Film Layer of LNOI/Si Hybrid Wafer Fabricated Using Low-Temperature Bonding Method. <i>Micromachines</i> , 2019, 10, 136.	2.9	15
54	Epitaxial Relations in Lattice-Matched (Ca, Sr)F ₂ Films Grown on GaAs{111} and Ge(111) Substrates. <i>Japanese Journal of Applied Physics</i> , 1984, 23, L803-L805.	1.5	14

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55	Improvement of the quality of Ge films on CaF ₂ /Si(111) structures by predeposited thin Ge layers. Surface Science, 1986, 174, 666-670.	1.9	14
56	Optimization of the Growth Conditions of Heteroepitaxial GaAs Films on CaF ₂ /Si Structures. Japanese Journal of Applied Physics, 1986, 25, L595-L598.	1.5	14
57	CMOS Application of Single-Grain Thin Film Transistor Produced Using Metal Imprint Technology. Japanese Journal of Applied Physics, 2003, 42, 1983-1987.	1.5	14
58	Field Electron Emission from Inkjet-Printed Carbon Black. Japanese Journal of Applied Physics, 2004, 43, 3923-3927.	1.5	14
59	Properties of Ink-Droplet Formation in Double-Gate Electrospray. Japanese Journal of Applied Physics, 2006, 45, 6475-6480.	1.5	14
60	Improvement of the Interface Properties of Fluoride/GaAs(100) Structures by Postgrowth Annealing. Japanese Journal of Applied Physics, 1988, 27, L2180-L2182.	1.5	13
61	Si Field Emitter Arrays Fabricated by Anodization and Transfer Technique. Japanese Journal of Applied Physics, 1997, 36, 7741-7744.	1.5	13
62	Influence of Direct Au-Bump Formation on Metal Oxide Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2002, 41, 2714-2719.	1.5	13
63	Pyramid Bumps for Fine-Pitch Chip-Stack Interconnection. Japanese Journal of Applied Physics, 2005, 44, 2751-2755.	1.5	13
64	Location Control of Si Thin-Film Grain Using Ni Imprint and Excimer Laser Annealing. Japanese Journal of Applied Physics, 2006, 45, 4335-4339.	1.5	13
65	Droplet Ejection Behavior in Electrostatic Inkjet Driving. Japanese Journal of Applied Physics, 2008, 47, 5281-5286.	1.5	13
66	Aluminum doping of 4H-SiC by irradiation of excimer laser in aluminum chloride solution. Japanese Journal of Applied Physics, 2014, 53, 06JF03.	1.5	13
67	Control of Crystal Orientations in Lattice-Mismatched SrF ₂ and (Ca, Sr)F ₂ Films on Si Substrates by Intermediate CaF ₂ Films. Japanese Journal of Applied Physics, 1985, 24, L56-L58.	1.5	12
68	Enhanced Solid-Phase Crystallization of Amorphous Si by Plasma Treatment Using Reactive Ion Etching. Japanese Journal of Applied Physics, 1997, 36, 1415-1419.	1.5	12
69	Cross-Hatch Related Oxidation and Its Impact on Performance of Strained-Si MOSFETs. Japanese Journal of Applied Physics, 2004, 43, 1886-1890.	1.5	12
70	Analysis of square-law detector for high-sensitive detection of terahertz waves. Journal of Applied Physics, 2019, 125, 174506.	2.5	12
71	Fabrication of a bonded LNOI waveguide structure on Si substrate using ultra-precision cutting. Japanese Journal of Applied Physics, 2020, 59, SBBD03.	1.5	12
72	Si/SiGe heterojunction collector for low loss operation of Trench IGBT. Applied Surface Science, 2004, 224, 399-404.	6.1	11

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73	Room-Temperature Bonding Using Mechanical Caulking Effect of Compliant Bumps for Chip-Stack Interconnection. Japanese Journal of Applied Physics, 2010, 49, 04DB02.	1.5	11
74	Room-temperature microjoining using ultrasonic bonding of compliant bump. , 2012, , .		11
75	Room-temperature bonding of heterogeneous materials for near-infrared image sensor. Japanese Journal of Applied Physics, 2014, 53, 04EB01.	1.5	11
76	In situ observation of ultrasonic flip-chip bonding using high-speed camera. Japanese Journal of Applied Physics, 2015, 54, 030204.	1.5	11
77	Control of Si Solid Phase Nucleation by Surface Steps for High-Performance Thin-Film Transistors. Japanese Journal of Applied Physics, 1993, 32, 482-485.	1.5	10
78	Imprint Lithography Using Triple-Layer-Resist and Its Application to Metal-Oxide-Silicon Field-Effect-Transistor Fabrication. Japanese Journal of Applied Physics, 2000, 39, 7080-7085.	1.5	10
79	Electrostatic Inkjet Printing of Carbon Nanotube for Cold Cathode Application. Japanese Journal of Applied Physics, 2008, 47, 5109-5112.	1.5	10
80	Morphology and semiconducting properties of homoepitaxially grown phosphorus-doped (100) and (111) diamond films by microwave plasma-assisted chemical vapor deposition using triethylphosphine as a dopant source. Journal of Crystal Growth, 1998, 191, 723-733.	1.5	9
81	Measurement of Dynamic Strain during Ultrasonic Au Bump Formation on Si Chip. Japanese Journal of Applied Physics, 2000, 39, 2478-2482.	1.5	9
82	Metal-Induced Lateral Crystallization of Amorphous Silicon under Reduced Nickel Supply. Solid State Phenomena, 2003, 93, 207-212.	0.3	9
83	Breakdown Voltage in Uniaxially Strained n-Channel SOI MOSFET. Japanese Journal of Applied Physics, 2004, 43, 2134-2139.	1.5	9
84	Inkjet-Printed Metal-Colloid-Induced Crystallization of Amorphous Silicon. Japanese Journal of Applied Physics, 2007, 46, 1263-1267.	1.5	9
85	Investigation on Characteristic Variation of Polycrystalline Silicon Thin-Film Transistor Using Laterally Grown Film. Japanese Journal of Applied Physics, 2009, 48, 03B014.	1.5	9
86	Ultrathin adhesive layer between LiNbO ₃ and SiO ₂ for bonded LNOI waveguide applications. Japanese Journal of Applied Physics, 2019, 58, SJJE06.	1.5	9
87	Improvement of Crystalline Quality of Si Films on CaF ₂ /Si Structures by Ion Implantation and Solid Phase Recrystallization. Japanese Journal of Applied Physics, 1983, 22, L118-L120.	1.5	8
88	Variation of Photoluminescence Properties of Stain-Etched Si with Crystallinity of Starting Polycrystalline Si Films. Japanese Journal of Applied Physics, 1994, 33, L1733-L1736.	1.5	8
89	Gas Species Dependent Charge Build-Up in Reactive Ion Etching. Japanese Journal of Applied Physics, 1996, 35, 6534-6539.	1.5	8
90	Single-crystal Si field emitter fabricated by anodization. Applied Physics Letters, 1997, 71, 983-985.	3.3	8

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91	Gated Si field emitter array prepared by using anodization. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 651.	1.6	8
92	Effect of Argon/Hydrogen Plasma Cleaning on Electroless Ni Deposition on Small-Area Al Pads. Japanese Journal of Applied Physics, 2010, 49, 08JA05.	1.5	8
93	Demonstration of GaN/LiNbO3 Hybrid Wafer Using Room-Temperature Surface Activated Bonding. ECS Journal of Solid State Science and Technology, 2020, 9, 045005.	1.8	8
94	Characteristics of Thin-Film Transistors Fabricated on Nucleation-Controlled Poly-Si Films by Surface Steps. Japanese Journal of Applied Physics, 1994, 33, 659-663.	1.5	7
95	A New Self-Aligned Process for Fabrication of Microemitter Arrays Using Selective Etching of Silicon. Japanese Journal of Applied Physics, 1996, 35, 6632-6636.	1.5	7
96	Electrical properties of homoepitaxial boron-doped diamond thin films grown by chemical vapor deposition using trimethylboron as dopant. Diamond and Related Materials, 1999, 8, 42-47.	3.9	7
97	Stamp technology for fabrication of field emitter from organic material. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 877.	1.6	7
98	Physical Random-Number Generator Using Schottky MOSFET. Japanese Journal of Applied Physics, 2002, 41, 2306-2311.	1.5	7
99	Fabrication of gated cold cathode using standing thin film induced by ion-beam bombardment. Journal of Vacuum Science & Technology B, 2006, 24, 932.	1.3	7
100	Single-Walled Carbon Nanotube Thin Film Transistor Fabricated Using Solution Prepared with 9,9-Dioctylfluorenyl-2,7-diylâ€“Bipyridine Copolymer. Japanese Journal of Applied Physics, 2011, 50, 070207.	1.5	7
101	Microjoining of LSI Chips on Poly(ethylene naphthalate) Using Compliant Bump. Japanese Journal of Applied Physics, 2011, 50, 06GM05.	1.5	7
102	Nitrogen doping of 4H-SiC by KrF excimer laser irradiation in liquid nitrogen. Japanese Journal of Applied Physics, 2015, 54, 04DP02.	1.5	7
103	Bonding dynamics of compliant microbump during ultrasonic bonding investigated by using Si strain gauge. Japanese Journal of Applied Physics, 2016, 55, 06GP22.	1.5	7
104	Increased doping depth of Al in wet-chemical laser doping of 4H-SiC by expanding laser pulse. Materials Science in Semiconductor Processing, 2017, 70, 193-196.	4.0	7
105	Epitaxial Growth of Fluoride Films on Silicon Substrates. Materials Research Society Symposia Proceedings, 1983, 25, 393.	0.1	6
106	Growth and Characterization of Compositionally Graded (Ca, Sr)F2Layers on Si(111) Substrates. Japanese Journal of Applied Physics, 1987, 26, 848-851.	1.5	6
107	Growth of single domain GaAs/fluoride/Si structures. Journal of Crystal Growth, 1989, 95, 398-402.	1.5	6
108	CMOS Image Sensor Using SOI-MOS/Photodiode Composite Photodetector Device. Japanese Journal of Applied Physics, 2002, 41, 2620-2624.	1.5	6

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109	Field emission from metal particles bound with a photoresist. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 552.	1.6	6
110	Low-Temperature High-Density Chip-Stack Interconnection Using Compliant Bump. , 2007, , .		6
111	Self-Heating of Laterally Grown Polycrystalline Silicon Thin-Film Transistor. Japanese Journal of Applied Physics, 2009, 48, 03B005.	1.5	6
112	Room-temperature high-density interconnection using ultrasonic bonding of cone bump for heterogeneous integration. , 2013, , .		6
113	n- and p-Type Doping of 4H-SiC by Wet-Chemical Laser Processing. Materials Science Forum, 0, 778-780, 645-648.	0.3	6
114	Radiation Damage in Epitaxial CaF ₂ Films on Si Substrates by Ar ⁺ Ion Implantation. Japanese Journal of Applied Physics, 1983, 22, L458-L460.	1.5	5
115	Formation of Ohmic Contacts to n-GaAs by Solid Phase Epitaxy of Evaporated and Ion Implanted Ge Films. Japanese Journal of Applied Physics, 1987, 26, 117-121.	1.5	5
116	Characterization of Ultrathin CaF ₂ Films Heteroepitaxially Grown on Si(111) Surfaces. Japanese Journal of Applied Physics, 1988, 27, L170-L172.	1.5	5
117	Electroplasticity memory devices using conducting polymers and solid polymer electrolytes. Polymer International, 1992, 27, 249-253.	3.1	5
118	SOI-MOSFET/Diode Composite Photodetection Device. Japanese Journal of Applied Physics, 2001, 40, 2897-2902.	1.5	5
119	Fabrication of Single-Crystal Silicon Field Emitter Array on Glass Substrate. Japanese Journal of Applied Physics, 2002, 41, 4307-4310.	1.5	5
120	Joule Heating of Field Emitter Tip Fabricated on Glass Substrate. Japanese Journal of Applied Physics, 2004, 43, 2749-2750.	1.5	5
121	Orientation Control of Location-Controlled Si Crystal Grain by Combining Ni Nano-Imprint and Excimer Laser Annealing with Si Double-Layer Process. Japanese Journal of Applied Physics, 2006, 45, L1293-L1295.	1.5	5
122	Room-temperature chip-stack interconnection using compliant bumps and wedge-incorporated electrodes. , 2010, , .		5
123	Room-Temperature Microjoining of LSI Chips on Poly(ethylene naphthalate) Film Using Mechanical Caulking of Au Cone Bump. Japanese Journal of Applied Physics, 2012, 51, 04DB04.	1.5	5
124	Analysis of room-temperature bonded compliant bump with ultrasonic bonding. , 2014, , .		5
125	Demonstration of ultraprecision ductile-mode cutting for lithium niobate microring waveguides. Japanese Journal of Applied Physics, 2016, 55, 110304.	1.5	5
126	Bonding of lithium niobate to silicon in ambient air using laser irradiation. Japanese Journal of Applied Physics, 2016, 55, 08RB09.	1.5	5

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127	Impact of subthreshold slope on sensitivity of square law detector for high frequency radio wave detection. Japanese Journal of Applied Physics, 2019, 58, SBBL05.	1.5	5
128	Ion-irradiation-enhanced dissolution of epitaxial fluoride films: A new class of inorganic single-crystal ion resist. Nuclear Instruments & Methods in Physics Research B, 1989, 39, 739-741.	1.4	4
129	Reduction of Charge Build-Up during Reactive Ion Etching by Using Silicon-On-Insulator Structures. Japanese Journal of Applied Physics, 1997, 36, 1505-1508.	1.5	4
130	CMOS Application of Schottky Source/Drain SOI MOSFET with Shallow Doped Extension. Japanese Journal of Applied Physics, 2004, 43, 2170-2175.	1.5	4
131	Nickel Metal Induced Lateral Crystallization of Patterned Amorphous Silicon Thin Film. Materials Science Forum, 2007, 561-565, 1149-1152.	0.3	4
132	Analysis and Fabrication of Ampere-Force Actuated Bistable Curved Beam. Japanese Journal of Applied Physics, 2009, 48, 06FK08.	1.5	4
133	Investigation of Enhanced Impact Ionization in Uniaxially Strained Si n-Channel Metal Oxide Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 04DC14.	1.5	4
134	Ultrasonic Bonding of Cone Bump for Integration of Large-Scale Integrated Circuits in Flexible Electronics. Japanese Journal of Applied Physics, 2013, 52, 05DB10.	1.5	4
135	Al doping of 4H-SiC by laser irradiation to coated Al film and its application to junction barrier Schottky diode. Japanese Journal of Applied Physics, 2016, 55, 04ER07.	1.5	4
136	Sensing local dynamic strain and temperature evolution during ultrasonic bonding of microbumps. , 2016, , .		4
137	InAs MOS-HEMT power detector for 1.0 THz on quartz glass. , 2017, , .		4
138	Dynamic Strain of Ultrasonic Cu and Au Ball Bonding Measured In-Situ by Using Silicon Piezoresistive Sensor. , 2017, , .		4
139	Formation of low resistance contacts to p-type 4H-SiC using laser doping with an Al thin-film dopant source. Japanese Journal of Applied Physics, 2019, 58, SDDF13.	1.5	4
140	Heteroepitaxial Growth of GaAs Films on CaF ₂ /Si(511) Structures Prepared with Rapid Thermal Annealing. Japanese Journal of Applied Physics, 1989, 28, 1784-1788.	1.5	3
141	Visualization of plasma uniformity in dry etching using the imaging plate. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 519.	1.6	3
142	Field emission characteristics of defect-controlled polyimide tunneling cathode. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1353.	1.6	3
143	Application of plasma oxidation to strained-Si/SiGe MOSFET. Materials Science in Semiconductor Processing, 2005, 8, 225-230.	4.0	3
144	Impact of Rapid Crystallization of Si Using Nickel-Metal-Induced Lateral Crystallization on Thin-Film Transistor Characteristics. Japanese Journal of Applied Physics, 2012, 51, 02BH04.	1.5	3

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145	Enhanced oxidation of Si using low-temperature oxidation catalyst SrTi _{1-x} Mg _x O ₃ . Japanese Journal of Applied Physics, 2016, 55, 06GJ05.	1.5	3
146	In-situ strain measurement of ultrasonic ball bonding. , 2016, , .		3
147	Microjoining of LSI Chips on Poly(ethylene naphthalate) Using Compliant Bump. Japanese Journal of Applied Physics, 2011, 50, 06CM05.	1.5	3
148	Ion Beam Bombardment Effect on Contacts in Solution-Processed Single-Walled Carbon Nanotube Thin Film Transistor. Japanese Journal of Applied Physics, 2011, 50, 098003.	1.5	3
149	Formation of Epitaxial Si Structures Using Alkaline Earth Fluoride Films. Materials Research Society Symposia Proceedings, 1985, 53, 129.	0.1	2
150	Suppressing Plasma Induced Degradation of Gate Oxide Using Silicon-on-Insulator Structures. Japanese Journal of Applied Physics, 1998, 37, 1278-1281.	1.5	2
151	Micro Field Emitter with Nano-Pillars Formed by Reactive Ion Etching of Photoresist. Japanese Journal of Applied Physics, 2003, 42, 4054-4058.	1.5	2
152	Wafer-Level Compliant Bump for 3D Chip-Stacking. International Power Modulator Symposium and High-Voltage Workshop, 2006, , .	0.0	2
153	Fabrication of Bistable Prestressed Curved-Beam. , 2007, , .		2
154	Low-temperature solid-phase crystallization of amorphous SiGe films on glass by imprint technique. Solid-State Electronics, 2008, 52, 1221-1224.	1.4	2
155	Oriented Growth of Location-Controlled Si Crystal Grains by Ni Nano-Imprint and Excimer Laser Annealing. Japanese Journal of Applied Physics, 2008, 47, 3036-3040.	1.5	2
156	Low-Temperature 3D Chip-Stacking Using Compliant Bump. , 2008, , .		2
157	Compliant bump technology for back-side illuminated CMOS image sensor. , 2009, , .		2
158	(Invited) Nano-Inkjet and Its Application to Metal-Induced Crystallization of a-Si for Poly-Si TFTs. ECS Transactions, 2010, 33, 149-156.	0.5	2
159	Grain filtering in MILC and its impact on performance of n- and p-channel TFTs. , 2010, , .		2
160	Low-temperature bonding of LSI chips to polymer substrate using Au cone bump for flexible electronics. , 2011, , .		2
161	Effect of Coating Self-Assembled Monolayer on Room-Temperature Bonding of Cu Micro-Interconnects. Japanese Journal of Applied Physics, 2013, 52, 068004.	1.5	2
162	Effect of laser annealing using high repetition rate pulsed laser on optical properties of phosphorus-ion-implanted ZnO nanorods. Applied Physics A: Materials Science and Processing, 2014, 114, 625-629.	2.3	2

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163	Room-temperature vacuum packaging using ultrasonic bonding with Cu compliant rim. , 2014, , .		2
164	Low-temperature oxidation of 4H-SiC using oxidation catalyst SrTi _{1-x} Mg _x O ₃ . Japanese Journal of Applied Physics, 2016, 55, 108001.	1.5	2
165	Room-Temperature Microjoining of LSI Chips on Poly(ethylene naphthalate) Film Using Mechanical Caulking of Au Cone Bump. Japanese Journal of Applied Physics, 2012, 51, 04DB04.	1.5	2
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